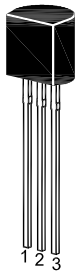
ST 2SA1266

PNP Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.
The transistor is subdivided into three groups, O, Y and G according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



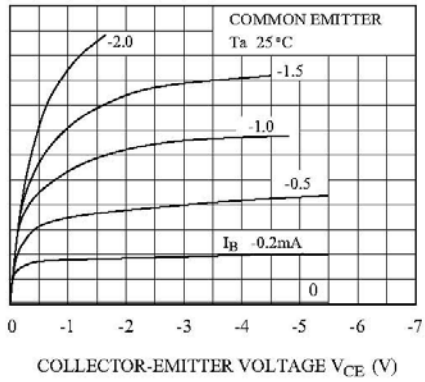
1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

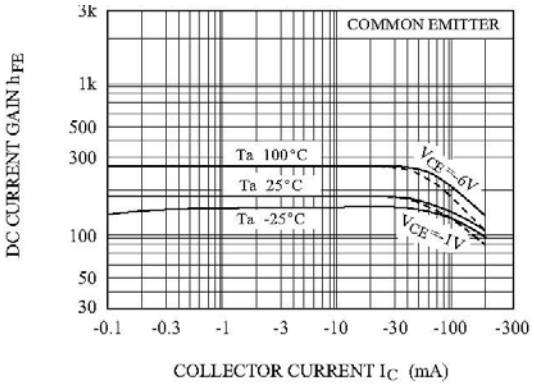
Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	150	mA
Base Current	$-I_B$	50	mA
Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

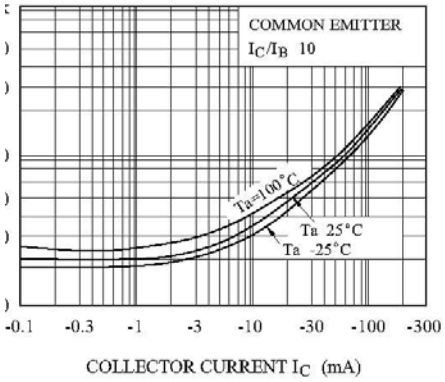
Characteristics at T_a = 25 °C

Parameter		Symbol	Min.	Max.	Unit
DC Current Gain					
at $-V_{CE}$ = 6 V, $-I_C$ = 2 mA	Current Gain Group O	h_{FE}	70	140	-
	Y	h_{FE}	120	240	-
	G	h_{FE}	200	400	-
at $-V_{CE}$ = 6 V, $-I_C$ = 150 mA		h_{FE}	25	-	-
Collector Base Cutoff Current at $-V_{CB}$ = 50 V		$-I_{CBO}$	-	0.1	µA
Emitter Base Cutoff Current at $-V_{EB}$ = 5 V		$-I_{EBO}$	-	0.1	µA
Collector Emitter Saturation Voltage at $-I_C$ = 100 mA, $-I_B$ = 10 mA		$-V_{CE(sat)}$	-	0.3	V
Base Emitter Saturation Voltage at $-I_C$ = 100 mA, $-I_B$ = 10 mA		$-V_{BE(sat)}$	-	1.1	V
Transition Frequency at $-V_{CE}$ = 10 V, $-I_C$ = 1 mA		f_T	80	-	MHz
Collector Output Capacitance at $-V_{CB}$ = 10 V, f = 1 MHz		C_{ob}	-	7	pF
Noise Figure at $-V_{CE}$ = 6 V, $-I_C$ = 0.1 V, f = 1 KHz, R_G = 10 KΩ		NF	-	10	dB

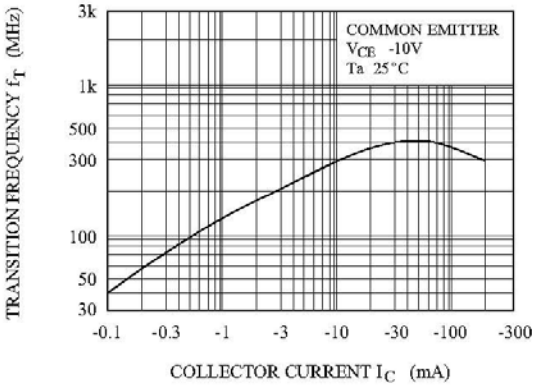




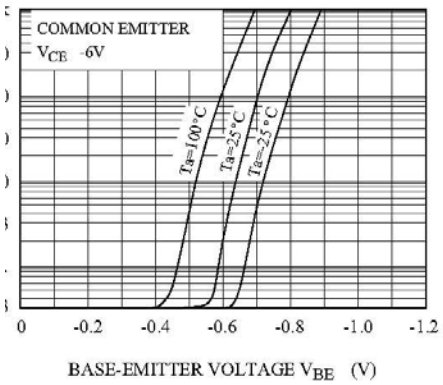
$V_{CE(sat)}$ - I_C



f_T - I_C



I_B - V_{BE}



P_C - T_a